

Performance

- Technology: 0.5um Power HEMT
- Frequency: 2.0~4.0GHz
- Typical Pout : 48.5dBm
- Typical Gain: 10dB
- Typical PAE: 48%
- Bias: 28V/-2.8V
- Package: Metal Ceramic

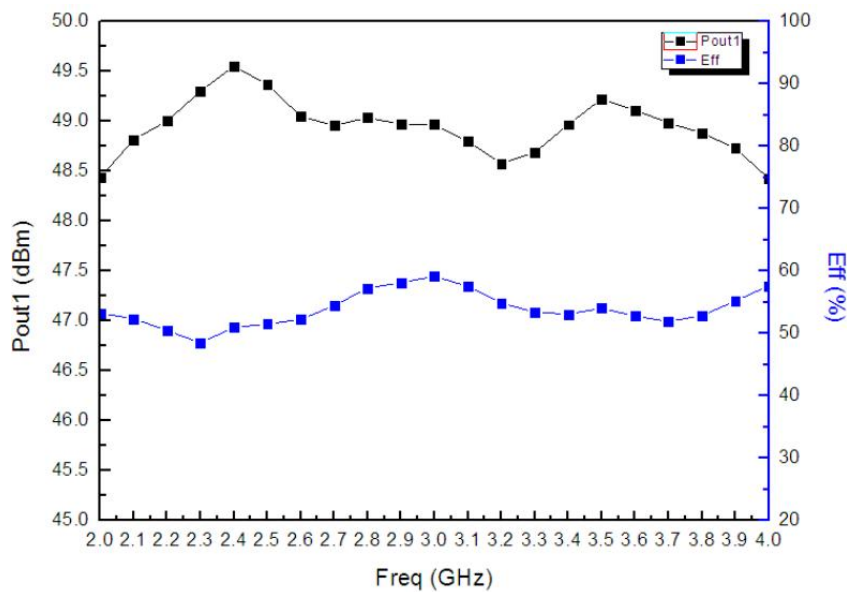


Electrical Specifications (TA=25°C,Vd=28V,Vg=-2.8V,F: 2.0~4.0GHz,CW,Interval=100MHz)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	-	48.5	-	dBm
Gp	Power Gain	-	10	-	dB
η_{add}	Power Added Efficiency	-	48	-	%
ΔGp	Gain Flatness	-0.8	-	+0.8	dB

Test Curves

Pout、Eff&Freq.

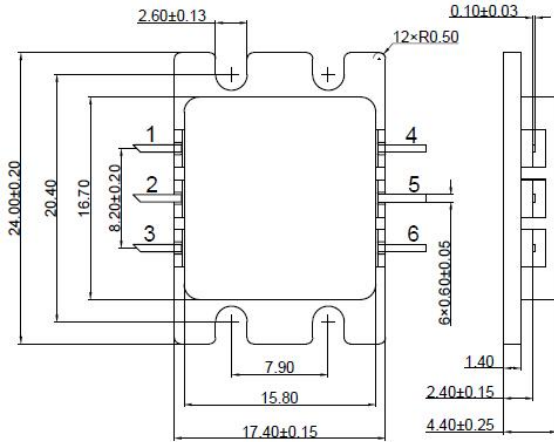


Absolute Max Ratings (TA=25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	36V	
Vg	Grid Voltage	-5V	
Tch	Channel Temperature	175°C	【1】
Tm	Mounting Temperature	300°C	1 min, N2 Protection
Tstg	Storage Temperature	-55~150°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.

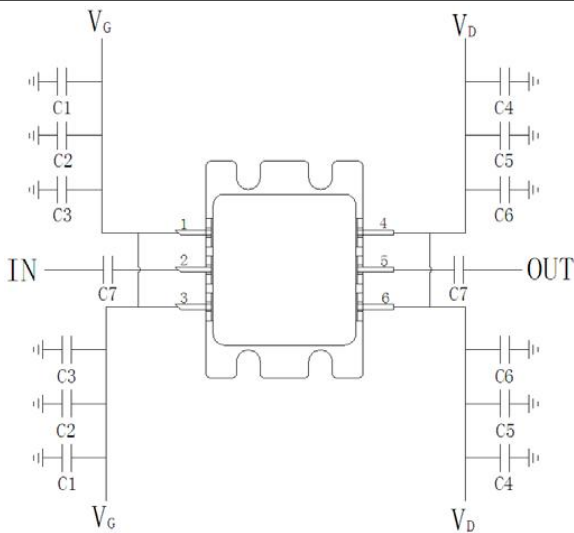
Outline Drawing



Pad Definition

No	Function	No	Function
1、3	Vg	4、6	Vd
2	RFin	5	RFout

Application Circuit



Symbol	Value
C1	100pF
C2	1000pF
C3	47uF
C4	100pF
C5	1000pF
C6	100uF
C7	20pF

Note:

- (1) The typical packaging form is C164-2 tube shell packaging;
- (2) Connect the circuit according to the diagram, pay attention to anti-static, and ensure good grounding and heat dissipation when using power devices;
- (3) In order to ensure good performance of the power module, the capacitance values of the power filter and energy storage capacitor should be reasonably selected according to the modulation method during pulse operation.